METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

ABSTRACT

A method of manufacturing a semiconductor device capable of improving adhesibility between a semiconductor layer and an electrode, while reducing contact resistance therebetween. A resist film is formed over the entire surface of an insulating layer formed by deposition or others. Then, in the resist film, provided is an opening corresponding to the p-side electrode pattern. Meanwhile, the residue of resist may attach to the opening, but is removed through light ashing treatments using oxygen, while a p-side contact layer is protected by the insulating layer. After that, with the resist film used as a mask, an opening in the insulating layer and a p-side electrode are formed by self-aligning. Damage to the surface of the p-side contact layer can be effectively suppressed. The p-side electrode can be formed on the clean surface of the p-side contact layer.

Fig.8